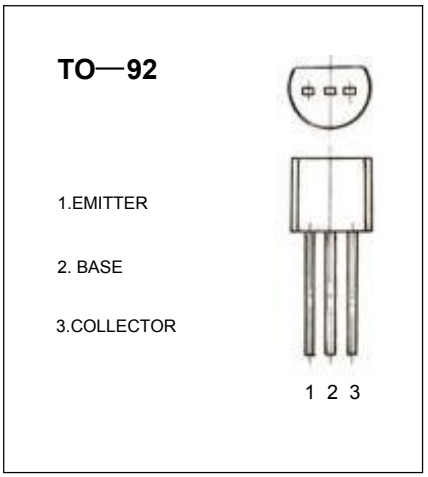
TO-92 Plastic-Encapsulate Transistors

S8550 TRANSISTOR（ NPN ）



FEATURES

Power dissipation

P_{CM}: 0.625 W（Tamb=25℃）

Collector current

I_{CM}: -0.5 A

Collector-base voltage

$V_{(BR)CBO}$: -40 V

Operating and storage junction temperature range

T_J，T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	I_C= 100μA，I_E=0	-40			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= 1 mA，I_B=0	-30			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= 100μA，I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}= 40 V，I_E=0			-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}= 30 V，I_B=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 3 V，I_C=0			-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}= 1 V，I_C= 30mA	70		400	
	$h_{FE(2)}$	V_{CE}= 1 V，I_C= 300mA	50			
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=500mA, I_B=50 mA			-0.5	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=500mA, I_B=50 mA			-1.2	V
Transition frequency	f_T	V_{CE}= 6 V, IC=20mA f =30MHz	150			MHz

CLASSIFICATION OF h_{FE} (1)

Rank	B	C	D
Range	70-140	120-240	200-400